



Figure 1: Sapphire surface structure annealed at 750°C (1) and 1550°C (2). Growth of Bi_2Se_3 on sapphire annealed at 750°C (3) and 1550°C (4). The sample grown on sapphire annealed at 1550°C appears to have less vertical island growth with slightly larger, less distinctive, domains. This sample also clearly grows on the same terraced step structure as the base sapphire.